

High frequency rectifier schottky barrier diode

RB081L-20

New

●Applications

High frequency rectification
For switching power supply

●Features

- 1) Compact power mold type (PMDS)
- 2) Extreme low forward voltage
(typical capability of 0.27V at 1A)
- 3) $I_o = 5A$ achieved despite the size

●Construction

Silicon epitaxial planar

●Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	25	V
DC reverse voltage	V_R	20	V
Mean rectifying current	I_{o1}^{*1}	5	A
	I_{o2}^{*2}	4	A
Peak forward surge current ($60\text{Hz} \cdot 1\text{ms}$)	I_{FSM}	70	A
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	$-40 \sim +125$	$^\circ\text{C}$

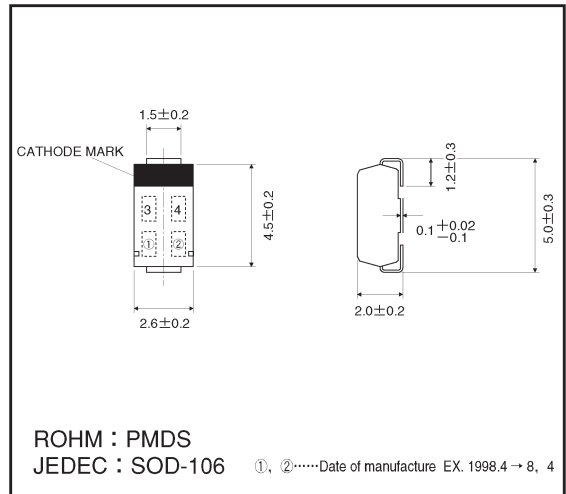
*1 When mounted on an alumina substrates, $T_c \text{ Max.} = 100^\circ\text{C}$

*2 When mounted on an alumina substrates, $T_a = 25^\circ\text{C}$

●Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	0.35	0.45	V	$I_F = 5.0A$
Reverse current	I_R	0.30	0.7	mA	$V_R = 20V$

●External dimensions (Units: mm)



●Electrical characteristic curves (Ta = 25°C unless specified otherwise)

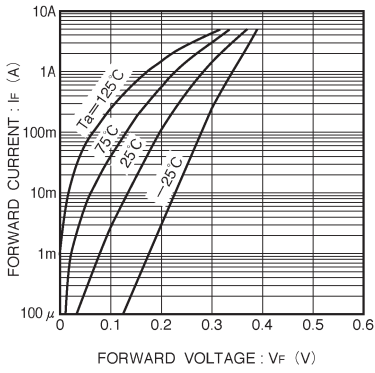


Fig. 1 Forward characteristics

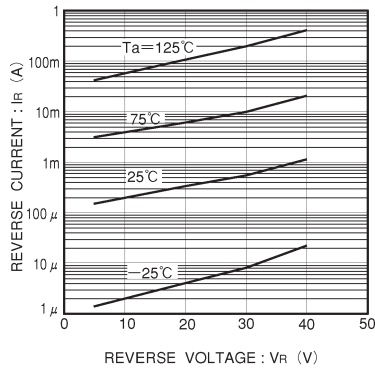


Fig. 2 Reverse characteristics

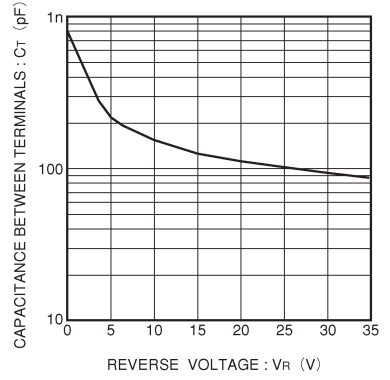


Fig. 3 Capacitance between terminals characteristics